

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild guestions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



December 2013

FQP2N60C / FQPF2N60C

N-Channel QFET® MOSFET

600 V, 2 A, 4.7 Ω

Description

This N-Channel enhancement mode power MOSFET is • 2 A, 600 V, $R_{DS(on)}$ = 4.7 Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 8.5 nC) resistance, and to provide superior switching performance

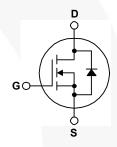
• Low Crss (Typ. 4.3 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- $I_D = 1 A$







Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP2N60C	FQPF2N60C	Unit
V_{DSS}	Drain-Source Voltage		600		V
I _D	Drain Current - Continuous (T _C = 25°C)		2.0	2.0 *	Α
	- Continuous (T _C = 100°C)		1.35	1.35 *	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	8	8 *	Α
V _{GSS}	Gate-Source Voltage		± 30		V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	120		mJ
I _{AR}	Avalanche Current	(Note 1)	2.0		Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	5.4		mJ
dv/dt	Peak Diode Recovery dv/dt (Note		4.5		V/ns
P_{D}	Power Dissipation (T _C = 25°C)		54	23	W
	- Derate above 25°C		0.43	0.18	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150		°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300		°C

^{*} Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FQP2N60C	FQPF2N60C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.32	5.5	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ, Max.	0.5		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP2N60C	FQP2N60C	TO-220	Tube	N/A	N/A	50 units
FQPF2N60C	FQPF2N60C	TO-220F	Tube	N/A	N/A	50 units

Flactrical Characteristics

Parameter	Test Conditions	Min.	Тур.	Max.	Unit
aracteristics					
Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	600			V
Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.6		V/°C
Zero Osto Valta va Brain Oversat	V _{DS} = 600 V, V _{GS} = 0 V			1	μΑ
Zero Gate Voltage Drain Current	V _{DS} = 480 V, T _C = 125°C			10	μА
Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	-		-100	nA
aracteristics					
	V _{DS} = V _{GS} , I _D = 250 μA	2.0		4.0	V
Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 1 A		3.6	4.7	Ω
Forward Transconductance	V _{DS} = 40 V, I _D = 1 A		5.0		S
ic Characteristics				1	
Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}.$		180	235	pF
Output Capacitance	f = 1.0 MHz		20	25	pF
Reverse Transfer Capacitance			4.3	5.6	pF
ing Characteristics					
ing Characteristics Turn-On Delay Time	V - 300 V I - 2 A		9	28	ns
	$V_{DD} = 300 \text{ V}, I_D = 2 \text{ A},$		9 25	28 60	ns ns
Turn-On Delay Time	$V_{DD} = 300 \text{ V}, I_{D} = 2 \text{ A},$ $R_{G} = 25 \Omega$				
Turn-On Delay Time Turn-On Rise Time			25	60	ns
Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time	$R_G = 25 \Omega$ (Note 4)		25 24	60 58	ns ns
Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time	$R_G = 25 \Omega$ (Note 4) $V_{DS} = 480 \text{ V, } I_D = 2 \text{ A,}$		25 24 28	60 58 66	ns ns ns
Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge	$R_G = 25 \Omega$ (Note 4)		25 24 28 8.5	60 58 66	ns ns ns
Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge	$R_{G} = 25 \Omega \tag{Note 4}$ $V_{DS} = 480 \text{V}, I_{D} = 2 \text{A},$ $V_{GS} = 10 \text{V} \tag{Note 4}$	 	25 24 28 8.5 1.3	60 58 66 12	ns ns ns nC
Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge	$R_{G} = 25 \Omega \end{tabular} \begin{tabular}{l} (Note 4) \\ V_{DS} = 480 V, I_{D} = 2 A, \\ V_{GS} = 10 V \end{tabular} \begin{tabular}{l} (Note 4) \\ (Note 4) \\ \end{tabular}$	 	25 24 28 8.5 1.3 4.1	60 58 66 12 	ns ns ns nC nC
Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge Source Diode Characteristics ar Maximum Continuous Drain-Source Dio	$R_G = 25 \Omega$ (Note 4) $V_{DS} = 480 \text{ V}, I_D = 2 \text{ A}, V_{GS} = 10 \text{ V}$ (Note 4) and Maximum Ratings are Forward Current		25 24 28 8.5 1.3 4.1	60 58 66 12 	ns ns ns nC nC
Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge Source Diode Characteristics ar Maximum Continuous Drain-Source Diode Fall Time	$R_G = 25 \Omega$ (Note 4) $V_{DS} = 480 \text{ V}, I_D = 2 \text{ A},$ $V_{GS} = 10 \text{ V}$ (Note 4) and Maximum Ratings of the Forward Current Forward Current		25 24 28 8.5 1.3 4.1	60 58 66 12 2 8	ns ns nc nC nC
Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge Source Diode Characteristics ar Maximum Continuous Drain-Source Dio	$R_G = 25 \Omega$ (Note 4) $V_{DS} = 480 \text{ V}, I_D = 2 \text{ A}, V_{GS} = 10 \text{ V}$ (Note 4) and Maximum Ratings are Forward Current		25 24 28 8.5 1.3 4.1	60 58 66 12 	ns ns ns nC nC
	Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current Gate-Body Leakage Current, Forward Gate-Body Leakage Current, Reverse aracteristics Gate Threshold Voltage Static Drain-Source On-Resistance Forward Transconductance ic Characteristics Input Capacitance Output Capacitance	Drain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}$, $I_D = 250 \text{ μA}$ Breakdown Voltage Temperature Coefficient $I_D = 250 \text{ μA}$, Referenced to 25° CZero Gate Voltage Drain Current $V_{DS} = 600 \text{ V}$, $V_{GS} = 0 \text{ V}$ Gate-Body Leakage Current, Forward Gate-Body Leakage Current, Reverse $V_{GS} = 30 \text{ V}$, $V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -30 \text{ V}$, $V_{DS} = 0 \text{ V}$ Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = 250 \text{ μA}$ Static Drain-Source On-Resistance $V_{GS} = 10 \text{ V}$, $I_D = 1 \text{ A}$ Forward Transconductance $V_{DS} = 40 \text{ V}$, $I_D = 1 \text{ A}$ ic CharacteristicsInput Capacitance $V_{DS} = 25 \text{ V}$, $V_{GS} = 0 \text$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Drain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}$, $I_D = 250 \text{ μA}$ 600Breakdown Voltage Temperature Coefficient $I_D = 250 \text{ μA}$, Referenced to 25°C 0.6Zero Gate Voltage Drain Current $V_{DS} = 600 \text{ V}$, $V_{GS} = 0 \text{ V}$ Gate-Body Leakage Current, Forward Gate-Body Leakage Current, Reverse $V_{GS} = 30 \text{ V}$, $V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -30 \text{ V}$, $V_{DS} = 0 \text{ V}$ Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = 250 \text{ μA}$ 2.0Static Drain-Source On-Resistance $V_{GS} = 10 \text{ V}$, $I_D = 1 \text{ A}$ 3.6Forward Transconductance $V_{DS} = 40 \text{ V}$, $I_D = 1 \text{ A}$ 5.0ic CharacteristicsInput Capacitance $V_{DS} = 25 \text{ V}$, $V_{GS} = 0 \text{ V}$, $V_{GS} =$	

- Notes: 1. Repetitive rating: pulse-width limited by maximum junction temperature. 2. L = 56 mH, I_{AS} = 2 A, V_{DD} = 50 V, R_{G} = 25 Ω , starting T_{J} = 25°C. 3. I_{SD} \leq 2 A, di/dt \leq 200 A/ μ s, V_{DD} \leq BV_{DSS}, starting T_{J} = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

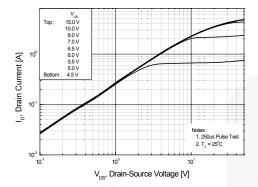


Figure 1. On-Region Characteristics

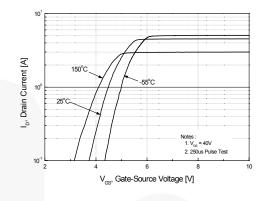


Figure 2. Transfer Characteristics

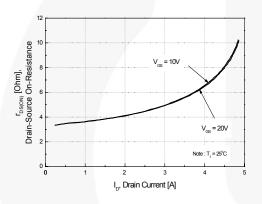


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

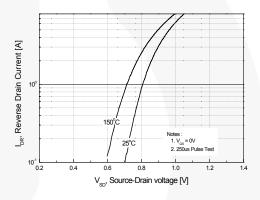


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

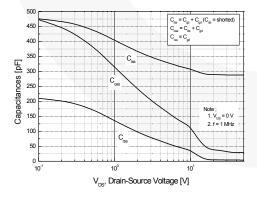


Figure 5. Capacitance Characteristics

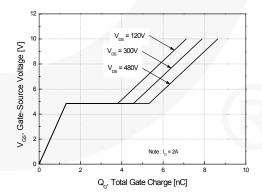


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

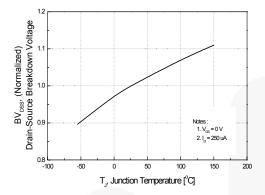


Figure 7. Breakdown Voltage Variation vs Temperature

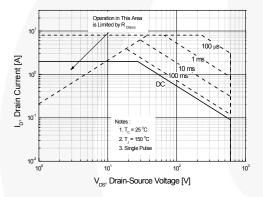


Figure 9-1. Maximum Safe Operating Area for FQP2N60C

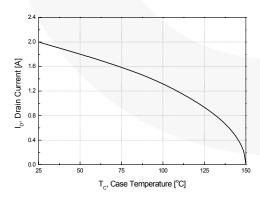


Figure 10. Maximum Drain Current vs Case Temperature

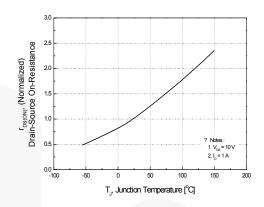


Figure 8. On-Resistance Variation vs Temperature

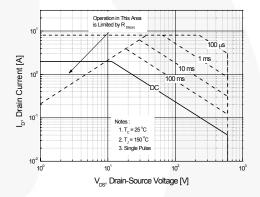


Figure 9-2. Maximum Safe Operating Area for FQPF2N60C

Typical Characteristics (Continued)

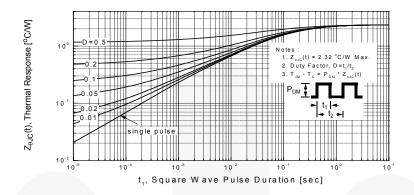


Figure 11-1. Transient Thermal Response Curve for FQP2N60C

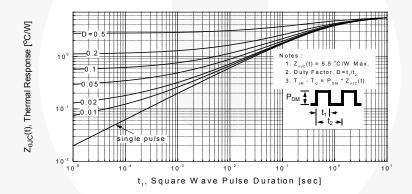


Figure 11-2. Transient Thermal Response Curve for FQPF2N60C

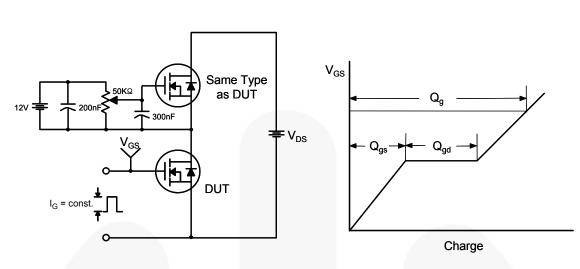


Figure 12. Gate Charge Test Circuit & Waveform

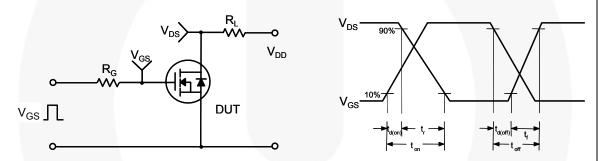


Figure 13. Resistive Switching Test Circuit & Waveforms

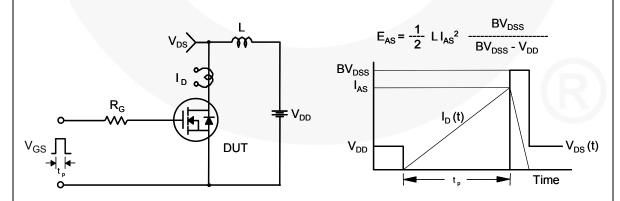
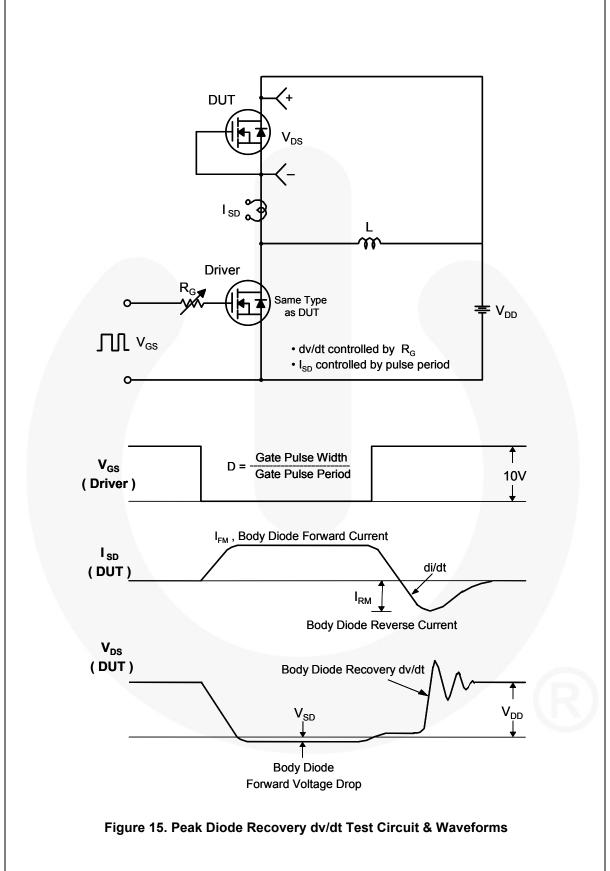


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

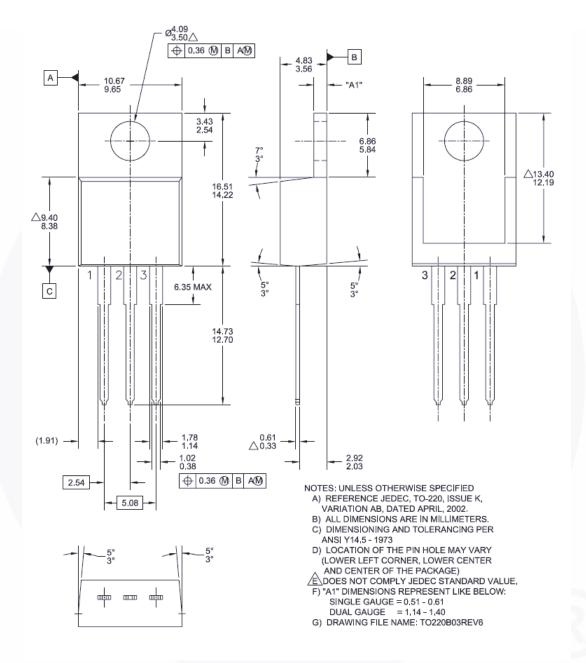


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT220-003

Mechanical Dimensions

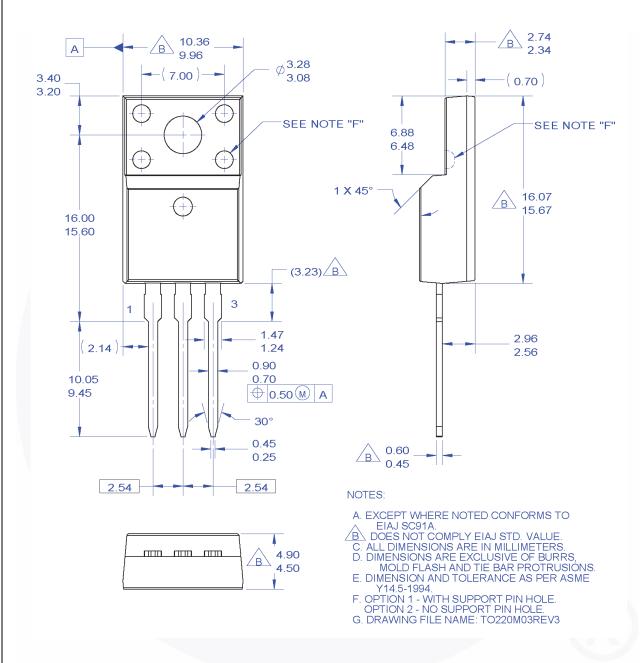


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TF220-003





TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™ AX-CAP® BitSiC™ Build it Now™ CorePLUS™ CorePOWER™ $CROSSVOLT^{\text{TM}}$

CTI ™ Current Transfer Logic™ DEUXPEED®

Dual Cool™ EcoSPARK® EfficentMax™

Fairchild[®]

ESBC™

Fairchild Semiconductor® FACT Quiet Series™

FACT® FAST® FastvCore™ FETBench™ FPS™

F-PFS™ FRFET®

Global Power ResourceSM GreenBridge™ Green FPS™

Green FPS™ e-Series™

G*max*™ GTO™ IntelliMAX™ ISOPLANAR™

Marking Small Speakers Sound Louder

and Better™ MegaBuck™ MICROCOUPLER™ MicroFET™

MicroPak™ MicroPak2™ MillerDrive™ MotionMax™ mWSaver® OptoHiT™ OPTOLOGIC®

OPTOPLANAR®

PowerTrench® PowerXS™ Programmable Active Droop™ **QFET** QS™

RapidConfigure™ Saving our world, 1mW/W/kW at a time™

SignalWise™ SmartMax™ SMART START™

Quiet Series™

Solutions for Your Success™

STEALTH™ SuperFET® SuperSOT™-3 SuperSOT™-6 SuperSOT™-8

SupreMOS® SvncFET™

SYSTEM®* TinyBoost[®]

Sync-Lock™

TinyBuck[®] TinyCalc™ TinyLogic[®] TINYOPTO™ TinvPower™ TinyPWM™ TinyWire™ TranSiC™ TriFault Detect™ TRUECURRENT®*

UHC[®] Ultra FRFET™ UniFFT™ VCX™ VisualMax™ VoltagePlus™

XS™

μSerDes™

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY
FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE
EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete Not In Production		Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. 166

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see any inability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and ex

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor: FQPF2N60C